

30 V, N-channel Trench MOSFET

14 March 2019

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	6.4	А
Static chara	octeristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 6.4 A; T <sub>j</sub> = 25 °C		-	17	24	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

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### 5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	D	drain		D			
2	D	drain					
3	G	gate		G ↓ ↓ ↓ ↓			
4	S	source	<b>TSOP6 (SOT457)</b>				
5	D	drain					
6	D	drain	1	$\rightarrow$			
				017aaa255			

### 6. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMN25ENEA	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457		

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMN25ENEA	J3

30 V, N-channel Trench MOSFET

### 8. Limiting values

#### Table 5. Limiting values

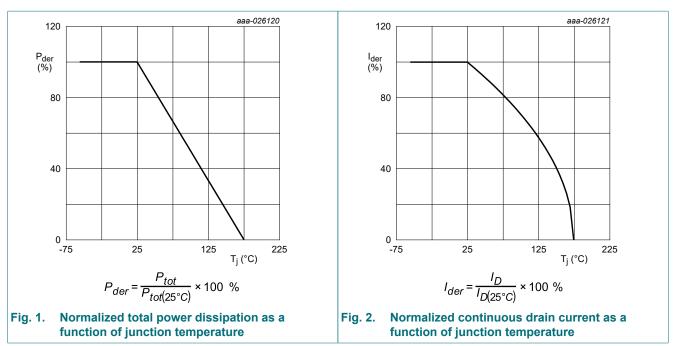
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	6.4	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	4.5	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	25	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	667	mW
			[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.5	А
ESD maximu	im rating					_
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche ru	ıggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$ T_{j(init)} = 25 \text{ °C}; I_D = 1.17 \text{ A}; \text{ DUT in}$ avalanche (unclamped)		-	17.4	mJ

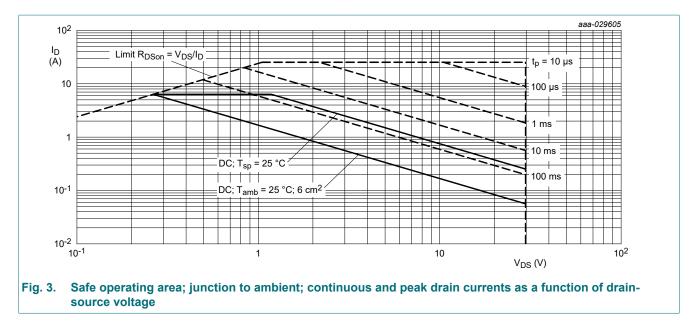
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins



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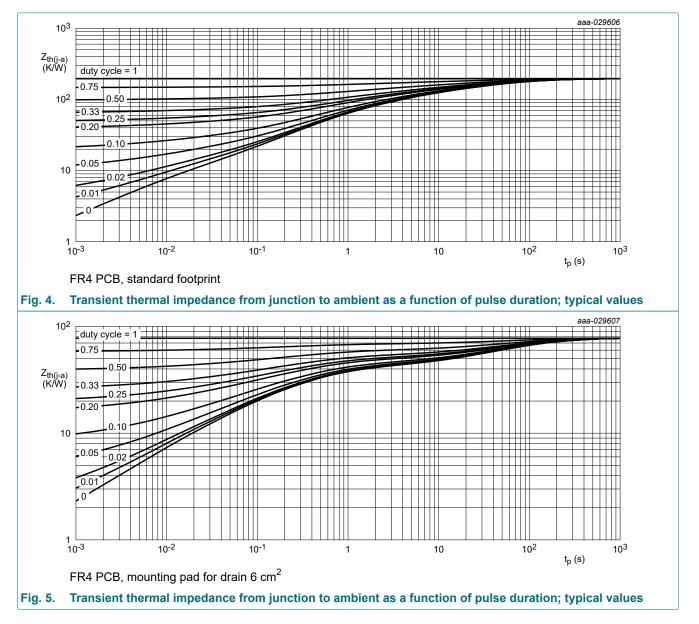


### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
μη-α)	thermal resistance from	in free air	[1]	-	195	225	K/W
	junction to ambient		[2]	-	78	90	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	15	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

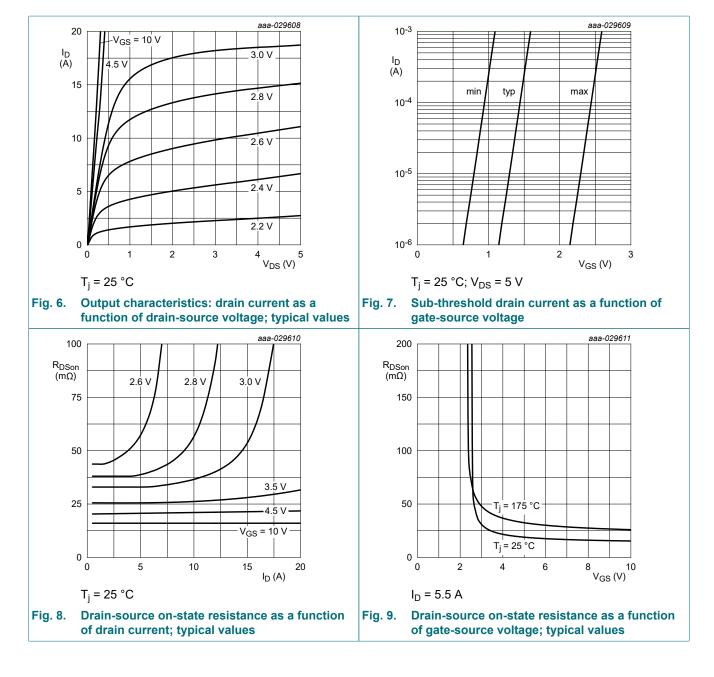
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



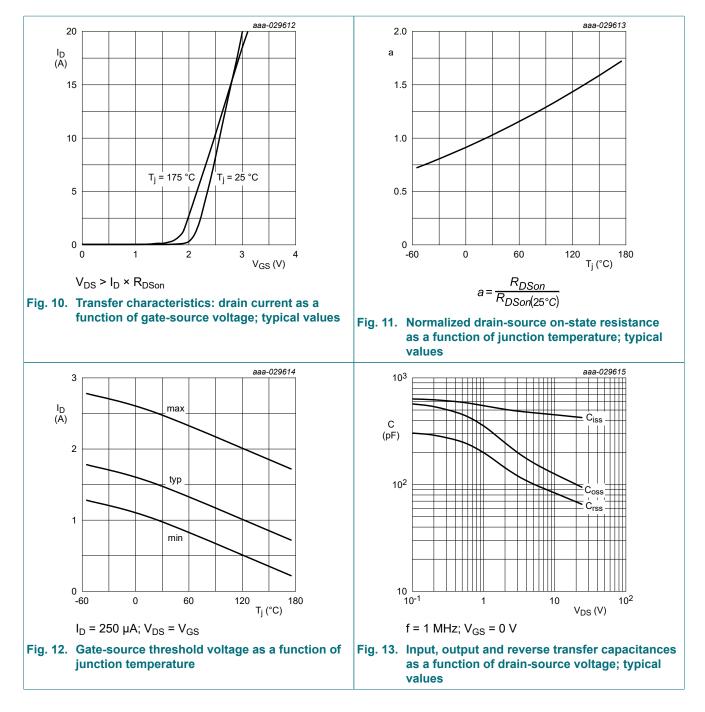
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1	1.5	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 6.4 A; T <sub>j</sub> = 25 °C	-	17	24	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 6.4 A; T <sub>j</sub> = 175 °C	-	29	41	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5.5 A; T <sub>j</sub> = 25 °C	-	22	32	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 6.4 A; T <sub>j</sub> = 25 °C	-	24	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 6.4 A; V <sub>GS</sub> = 10 V;	-	9.5	14	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
Q <sub>GD</sub>	gate-drain charge	1 1	-	2.15	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	440	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	110	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	75	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 6.4 A; V <sub>GS</sub> = 10 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	18	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 [	-	15	-	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-drai	n diode		1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 1.5 A; dI <sub>S</sub> /dt = -100 A/µs;	-	11	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C	-	4	-	nC

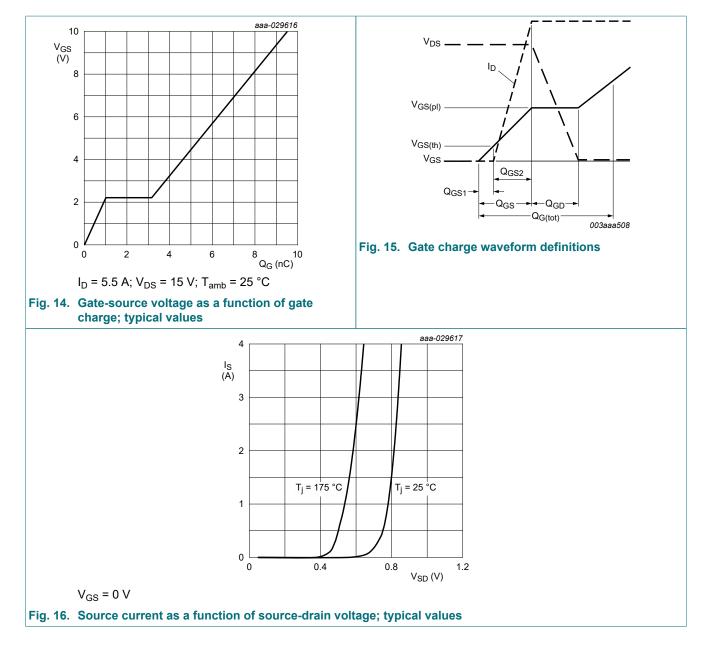
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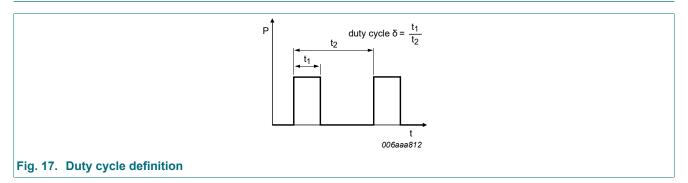
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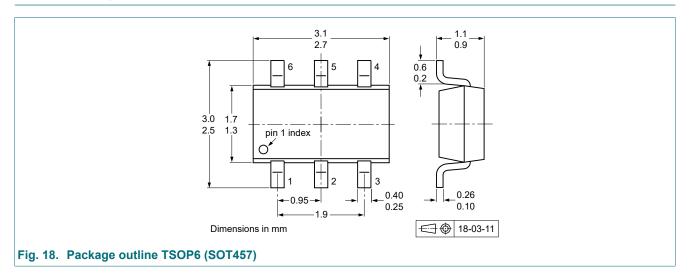
### **11. Test information**



#### **Quality information**

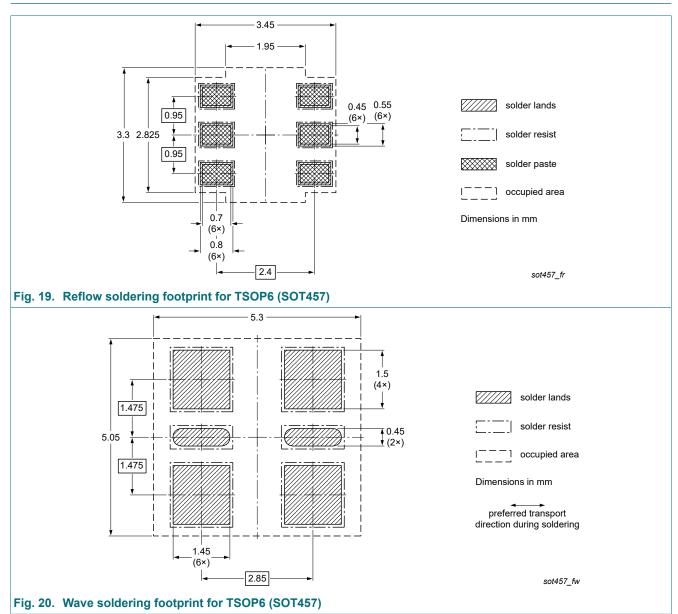
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



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### 13. Soldering



PMN25ENEA

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### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMN25ENEA v.1	20190314	Product data sheet	-	-		

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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